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Erratum

Erratum to “Laser induced down conversion optical characterizations of synthesized $Zn_{2-x}Mn_xSiO_4$ ($0.5 \leq x \leq 5$ mol%) nanophosphors” [J. Alloys Compd. 473 (2009) 483–489]

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In the previous trap-depth value calculations, the value of escape frequency (S) instead of 10^9 in Eq. (3) on p. 485 the 10^{-9} was mistakenly used. Therefore, the values in Table 4 are modified.

Table 4
Trap-depth values for $Zn_2SiO_4:Mn^{2+}$ nanophosphor at different temperatures.

Zn_2SiO_4:M (mol%)	Trap depth values (eV)								
	800 °C			900 °C			1000 °C		
	E_1	E_2	E_3	E_1	E_2	E_3	E_1	E_2	E_3
Mn (0.5)	0.234	0.254	0.287	0.242	0.260	0.289	0.245	0.265	0.291
Mn (1)	0.232	0.253	0.285	0.238	0.259	0.287	0.244	0.264	0.291
Mn (2)	0.231	0.252	0.284	0.237	0.257	0.287	0.243	0.263	0.289
Mn (3)	0.231	0.251	0.284	0.235	0.256	0.286	0.242	0.261	0.287
Mn (4)	0.229	0.251	0.284	0.234	0.253	0.286	0.242	0.261	0.287
Mn (5)	0.228	0.251	0.283	0.233	0.251	0.285	0.241	0.261	0.287

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